

### MG06100S-BR1MM




#### Features

- Ultra Low Loss
- High Ruggedness
- High Short Circuit Capability
- Positive Temperature Coefficient
- With Fast Free-Wheeling Diodes

#### Applications

- Inverter
- Converter
- Welder
- SMPS and UPS
- Induction Heating

#### Agency Approvals

AGENCY	AGENCY FILE NUMBER
	E71639

#### Module Characteristics ( $T_c = 25^\circ\text{C}$ , unless otherwise specified)

Symbol	Parameters	Test Conditions	Min	Typ	Max	Unit
$R_{thJC}$	Junction-to-Case Thermal Resistance	Per IGBT			0.2	K/W
$R_{thJD}$		Per Inverse Diode			0.5	K/W
Torque	Module-to-Sink	Recommended (M6)	3		5	N-m
Torque	Module Electrodes	Recommended (M5)	2.5		5	N-m
Weight				150		g

#### Absolute Maximum Ratings ( $T_c = 25^\circ\text{C}$ , unless otherwise specified)

Symbol	Parameters	Test Conditions	Values	Unit
<b>IGBT</b>				
$V_{CES}$	Collector - Emitter Voltage		600	V
$V_{GES}$	Gate - Emitter Voltage		$\pm 20$	V
$I_c$	DC Collector Current	$T_c=25^\circ\text{C}$	150	A
		$T_c=80^\circ\text{C}$	105	A
$I_{cpuls}$	Pulsed Collector Current	$T_c=25^\circ\text{C}, t_p=1\text{ms}$	300	A
		$T_c=80^\circ\text{C}, t_p=1\text{ms}$	210	
$P_{tot}$	Power Dissipation Per IGBT		625	W
$T_J$	Junction Temperature Range		-40 to +150	$^\circ\text{C}$
$T_{STG}$	Storage Temperature Range		-40 to +125	$^\circ\text{C}$
$V_{isol}$	Insulation Test Voltage	AC, $t=1\text{min}$	3000	V
<b>Diode</b>				
$V_{RRM}$	Repetitive Reverse Voltage		600	V
$I_{F(AV)}$	Average Forward Current	$T_c=25^\circ\text{C}$	125	A
		$T_c=80^\circ\text{C}$	85	A
$I_{F(RMS)}$	RMS Forward Current		122	A
$I_{FSM}$	Non-Repetitive Surge Forward Current	$T_J=45^\circ\text{C}, t=10\text{ms}$ , Sine	500	A
		$T_J=45^\circ\text{C}, t=8.3\text{ms}$ , Sine	545	

Life Support Note:

#### Not Intended for Use in Life Support or Life Saving Applications

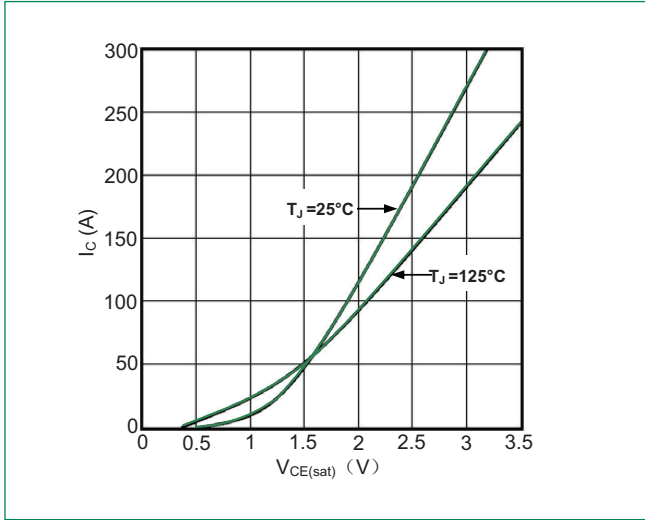
The products shown herein are not designed for use in life sustaining or life saving applications unless otherwise expressly indicated.

MG06100S-BR1MM

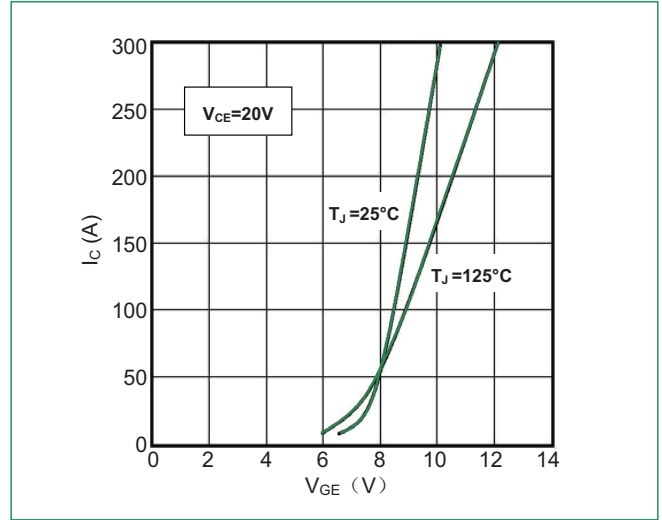
### Electrical and Thermal Specifications ( $T_c = 25^\circ\text{C}$ , unless otherwise specified)

Symbol	Parameters	Test Conditions	Min	Typ	Max	Unit
<b>IGBT</b>						
$V_{GE(th)}$	Gate - Emitter Threshold Voltage	$V_{CE}=V_{GE}, I_C=250\mu\text{A}$	3.5		5.5	V
$V_{CE(sat)}$	Collector - Emitter Saturation Voltage	$I_C=100\text{A}, V_{GE}=15\text{V}, T_J=25^\circ\text{C}$		1.9		V
		$I_C=100\text{A}, V_{GE}=15\text{V}, T_J=125^\circ\text{C}$		2.1		V
$I_{CES}$	Collector Leakage Current	$V_{CE}=600\text{V}, V_{GE}=0\text{V}, T_J=25^\circ\text{C}$			0.5	mA
		$V_{CE}=600\text{V}, V_{GE}=0\text{V}, T_J=125^\circ\text{C}$		3		mA
$I_{GES}$	Gate Leakage Current	$V_{CE}=0\text{V}, V_{GE}=\pm 20\text{V}$	-1.1		1.1	$\mu\text{A}$
$Q_{ge}$	Gate Charge	$V_{CC}=300\text{V}, I_C=100\text{A}, V_{GE}=\pm 15\text{V}$		230		nC
$C_{ies}$	Input Capacitance	$V_{CE}=25\text{V}, V_{GE}=0\text{V}, f=1\text{MHz}$		5.3		nF
$C_{oes}$	Output Capacitance			0.52		
$C_{res}$	Reverse Transfer Capacitance			0.34		
$t_{d(on)}$	Turn - on Delay Time	$V_{CC}=300\text{V}$ $I_C=100\text{A}$ $R_G=10\Omega$ $V_{GE}=\pm 15\text{V}$ Inductive Load	$T_J=25^\circ\text{C}$		45	ns
			$T_J=125^\circ\text{C}$		50	ns
$t_r$	Rise Time		$T_J=25^\circ\text{C}$		45	ns
			$T_J=125^\circ\text{C}$		45	ns
$t_{d(off)}$	Turn - off Delay Time		$T_J=25^\circ\text{C}$		320	ns
			$T_J=125^\circ\text{C}$		350	ns
$t_f$	Fall Time		$T_J=25^\circ\text{C}$		35	ns
			$T_J=125^\circ\text{C}$		40	ns
$E_{on}$	Turn - on Energy		$T_J=25^\circ\text{C}$		3.5	mJ
			$T_J=125^\circ\text{C}$		4.5	mJ
$E_{off}$	Turn - off Energy	$T_J=25^\circ\text{C}$		2.5	mJ	
		$T_J=125^\circ\text{C}$		3.5	mJ	
<b>Diode</b>						
$V_F$	Forward Voltage	$I_F=100\text{A}, V_{GE}=0\text{V}, T_J=25^\circ\text{C}$		1.9	2.2	V
		$I_F=100\text{A}, V_{GE}=0\text{V}, T_J=125^\circ\text{C}$		1.7	2.0	V
$t_{rr}$	Reverse Recovery Time	$I_F=100\text{A}, V_R=400\text{V}$ $di_P/dt=-1000\text{A}/\mu\text{s}$ $T_J=125^\circ\text{C}$		50		ns
$I_{RRM}$	Max. Reverse Recovery Current			45		A
$Q_{rr}$	Reverse Recovery Charge			1.5		$\mu\text{C}$

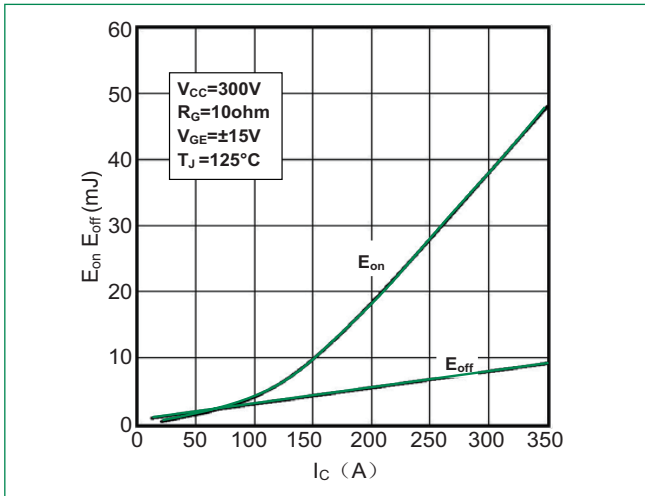
**Figure 1: Typical Output Characteristics**



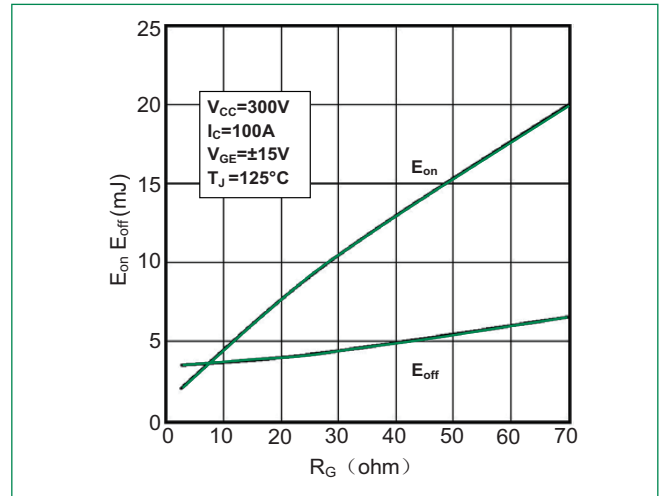
**Figure 2: Typical Transfer characteristics**



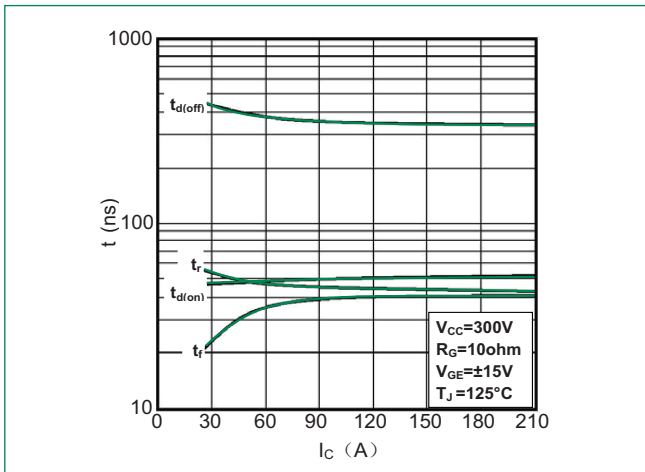
**Figure 3: Switching Energy vs. Collector Current**



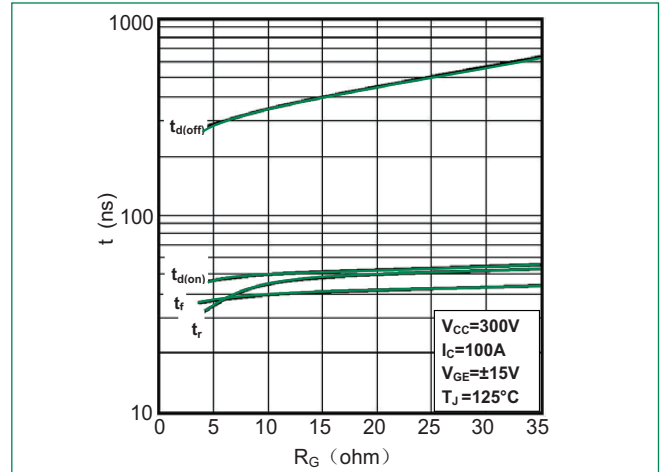
**Figure 4: Switching Energy vs. Gate Resistor**



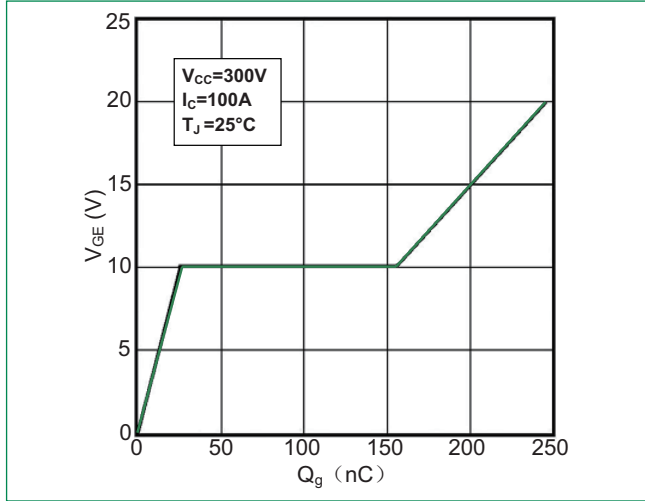
**Figure 5: Switching Times vs. Collector Current**



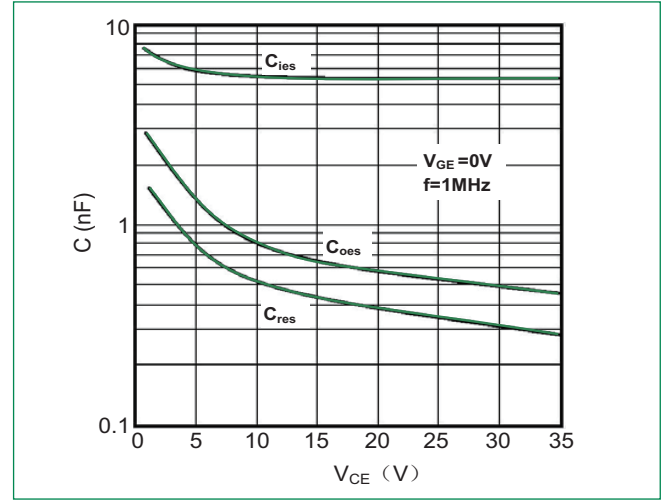
**Figure 6: Switching Times vs. Gate Resistor**



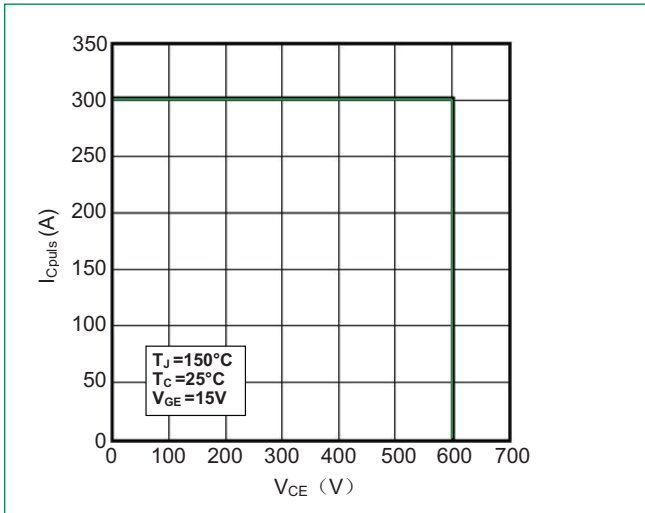
**Figure 7: Gate Charge characteristics**



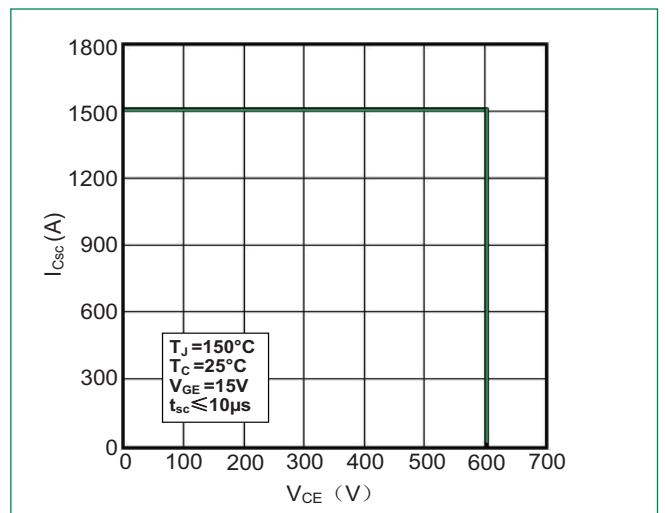
**Figure 8: Typical Capacitances vs.  $V_{CE}$**



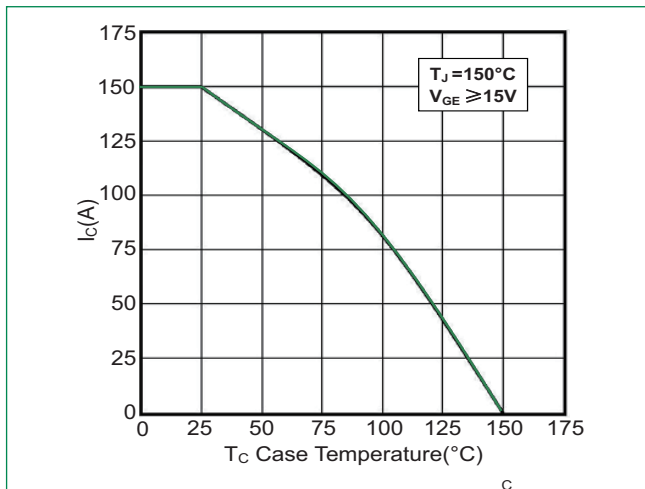
**Figure 9: Reverse Biased Safe Operating Area**



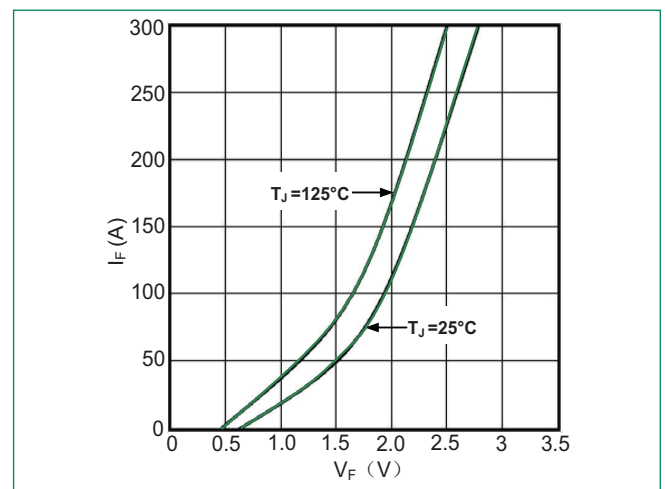
**Figure 10: Short Circuit Safe Operating Area**



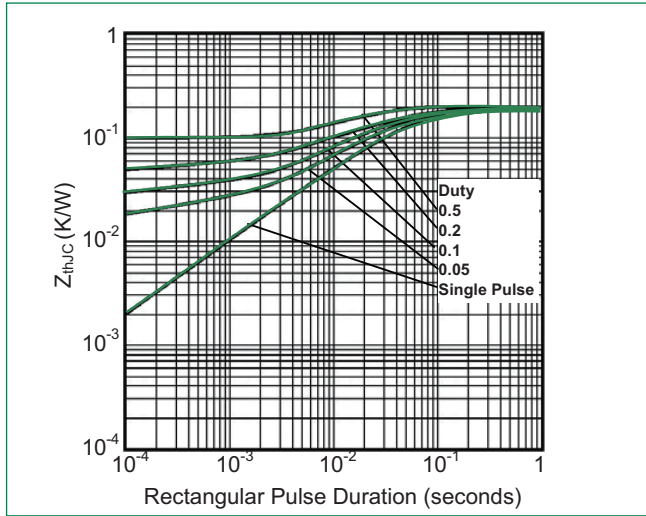
**Figure 11: Rated Current vs.  $T_c$**



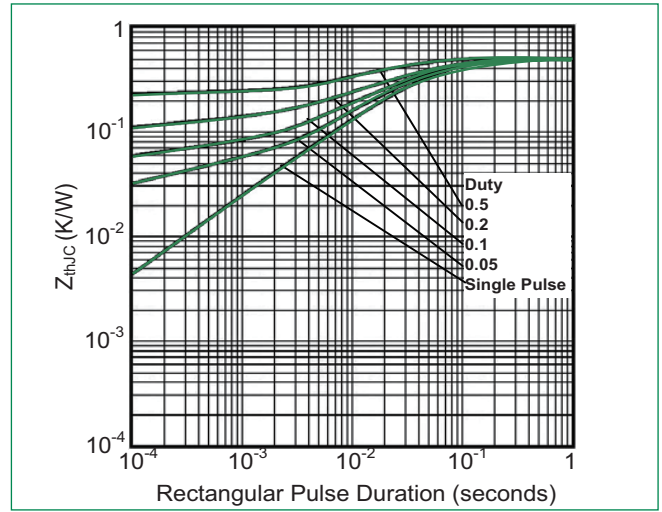
**Figure 12: Diode Forward Characteristics**



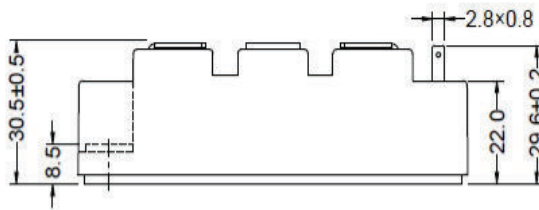
**Figure 13: Transient Thermal Impedance of IGBT**



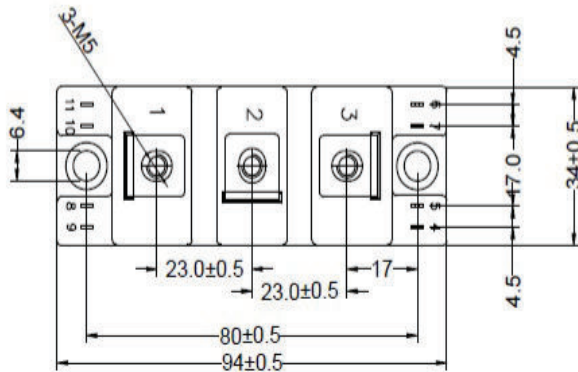
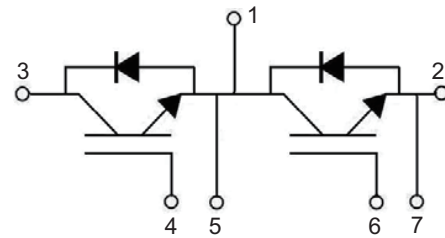
**Figure 14: Transient Thermal Impedance of Diode**



**Dimensions-Package S**



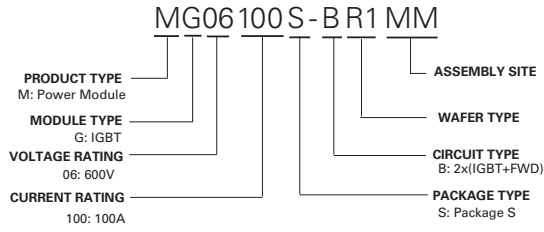
**Circuit Diagram**



**Packing Options**

Part Number	Marking	Weight	Packing Mode	M.O.Q
MG06100S-BR1MM	MG06100S-BR1MM	150g	Bulk Pack	100

**Part Numbering System**



**Part Marking System**

